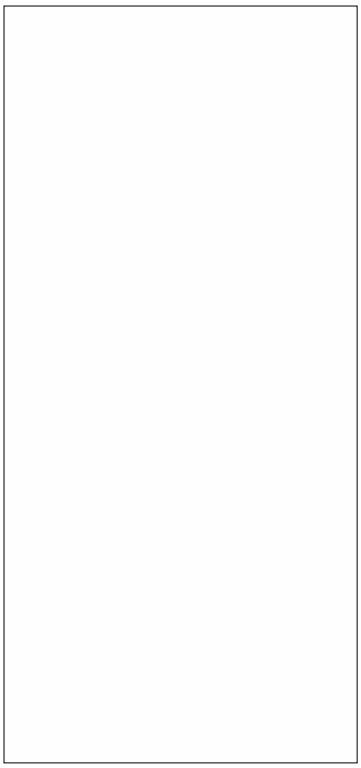
DESCRIPTION:

With high ability to withstand



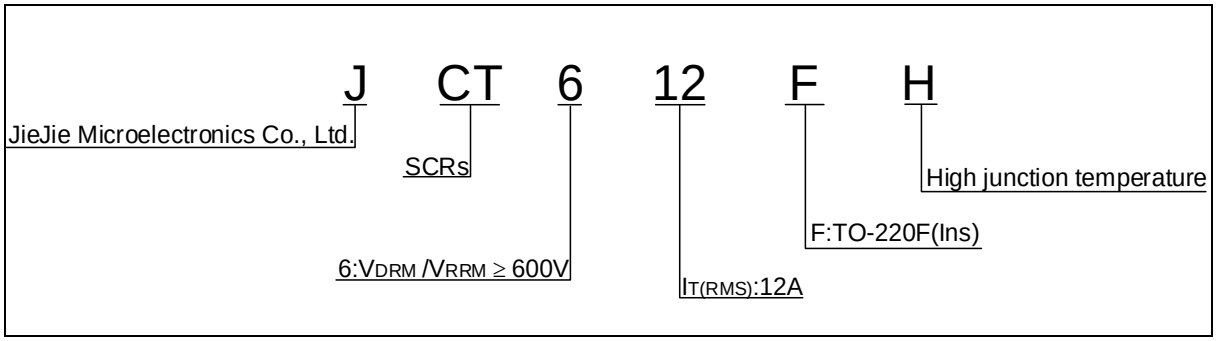
Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

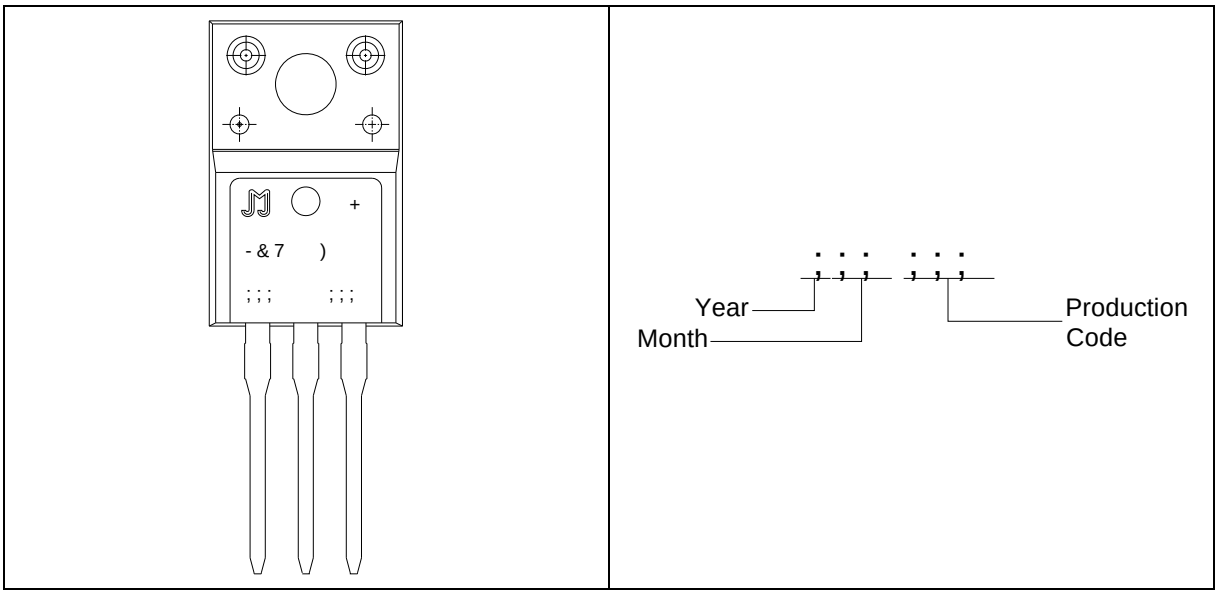
I_{GT}	V_D=12V R_L=33Ω	-	-	15	mA
V_{GT}		-	-	1	V
V_{GD}	V_D=V_{DRM} T_j=150 R_L=3.3kΩ	0.2	-	-	V

I_L V

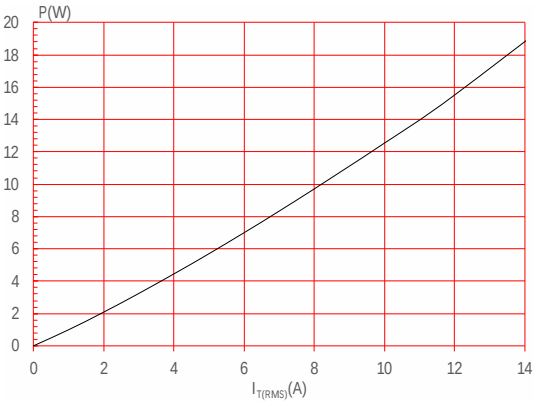
ORDERING INFORMATION



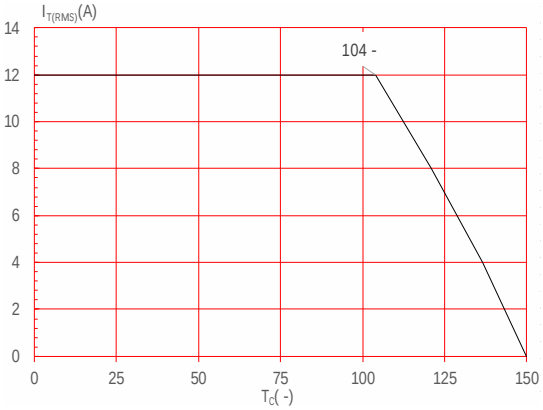
MARKING



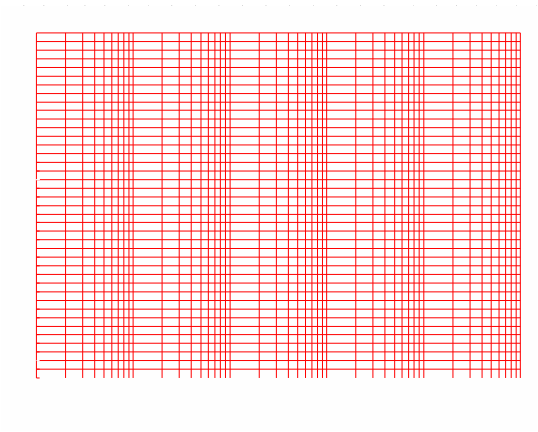
Maximum power dissipation versus RMS on-state current



RMS on-state current versus case temperature

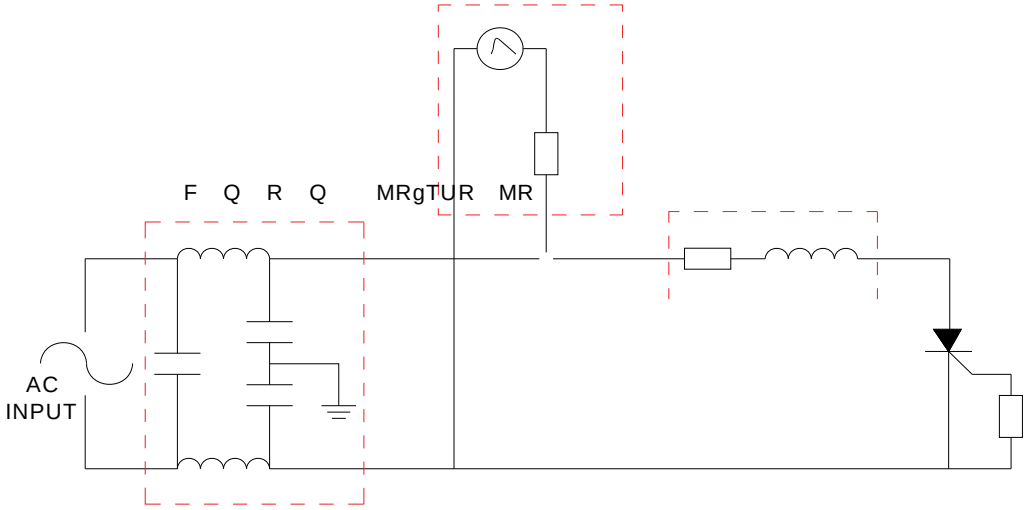


Surge peak on-state current versus number of cycles



On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



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Date	Revision	Changes
Jun.12, 2023	A.1.0	Last update
Oct.17, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

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